503089439 12/07/2014

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2

EPAS ID: PAT3136044

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
Chia-Lin Lu	12/02/2014
Chun-Lung Chen	12/02/2014
Kun-Yuan Liao	12/02/2014
Feng-Yi Chang	12/02/2014
En-Chiuan Liou	12/02/2014
Chieh-Te Chen	12/02/2014

RECEIVING PARTY DATA

Name:	UNITED MICROELECTRONICS CORP.	
Street Address:	Street Address: No.3, Li-Hsin Road 2, Science-Based Industrial Park	
City:	Hsin-Chu City	
State/Country:	TAIWAN	

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	14562768

CORRESPONDENCE DATA

Fax Number: (703)997-4517

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Phone: 3027291562

Patent.admin.uspto.cr@naipo.com Email:

Correspondent Name: WINSTON HSU Address Line 1: P.O.BOX 506

Address Line 4: MERRIFIELD, VIRGINIA 22116

ATTORNEY DOCKET NUMBER:	NAUP2377USA
NAME OF SUBMITTER:	KATE YEH
SIGNATURE:	/KATE YEH/
DATE SIGNED:	12/07/2014

Total Attachments: 12 source=2123273#page1.tif source=2123273#page2.tif

source=2123273#page3.tif		
source=2123273#page4.tif		
source=2123273#page5.tif		
source=2123273#page6.tif		
source=2123273#page7.tif		
source=2123273#page8.tif		
source=2123273#page9.tif		
source=2123273#page10.tif		
source=2123273#page11.tif		
source=2123273#page12.tif		

Title of Invention: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	_filed on,	or
☐ PCT international application	n number	filed on	
The above-identified application was	made or authorized to be made	by me.	
I believe that I am the original invent application.	or or an original joint inventor of a	a claimed invention in the	
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr	I false statement made in this de- isonment of not more than five (5	claration is punishable) years, or both.	
In consideration of the payment by	UNITED MICROELECTROI	NICS having a postal addr	ess of
No.3, Li-Hsin Road 2, Science	-Based Industrial Park, Hs	in-Chu City 300, Taiwan,	R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	o I of the sum of One Dollar (\$ 1.0 and valuable consideration.	00), the receipt of which is her	eby
I hereby sell, assign and transfer to a the entire right, title and interest in a invention as above-identified applica invention by the above application or substitutes, or extensions thereof, ar	nd to any and all improvements w tion and, in and to, all Letters Par any continuations, continuation-	which are disclosed in the tent to be obtained for said in-part, divisions, renewals,	E
I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or encumbrar n this assignment;	nce has been or will be made o	or
I further covenant that ASSIGNEE w and documents relating to said inver known and accessible to I and will te related thereto and will promptly exe	ntion and said Letters Patent and stify as to the same in any interfe	legal equivalents as may be erence, litigation proceeding	s
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be no IN WINTNESS WHEREOF, I have he	olication, said invention and said lecessary or desirable to carry out	Letters Patent and said the proposes thereof.	signing)
Note: An application data sheet (PTC inventive entity, must accompany this			

Page 1 of 12

NPO#NAU-P2377-USA:0 CUST#UMCD-2014-0517

LEGAL NAM	WE OF MAKEN LOKING	'IN)	
Inventor:	Chia-Lin Lu	Date:	DEC 0 2 2014
Signature:	Chia-Lin		

Page 2 of 12

NPO#NAU-P2377-USA:0 CUST#UMCD-2014-0517

Title of Invention: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	_filed on,	or
☐ PCT international application	number	filed on	
The above-identified application was	made or authorized to be made	by me.	
I believe that I am the original invent application.	or or an original joint inventor of a	claimed invention in the	
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr	I false statement made in this dec isonment of not more than five (5)	laration is punishable years, or both.	
In consideration of the payment by	UNITED MICROELECTRON CORP.	IICS having a postal addr	ress of
No.3, Li-Hsin Road 2, Science	-Based Industrial Park, Hsi	n-Chu City 300, Taiwan,	R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an		0), the receipt of which is her	eby
I hereby sell, assign and transfer to A the entire right, title and interest in an invention as above-identified applica invention by the above application or substitutes, or extensions thereof, an	nd to any and all improvements w tion and, in and to, all Letters Pate any continuations, continuation-i	hich are disclosed in the ent to be obtained for said n-part, divisions, renewals,	ĒĒ
I hereby covenant that no assignmer entered into which would conflict with	nt, sale, agreement or encumbran n this assignment;	ce has been or will be made o	or
I further covenant that ASSIGNEE w and documents relating to said inven known and accessible to I and will te related thereto and will promptly exec	ition and said Letters Patent and I stify as to the same in any interfe	egal equivalents as may be rence, litigation proceeding	S
representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be no IN WINTNESS WHEREOF, I have he	lication, said invention and said L cessary or desirable to carry out t	etters Patent and said the proposes thereof.	f signing)
Note: An application data sheet (PTC inventive entity, must accompany this	D/SB/14 or equivalent), including r s form. Use this form for each add	naming the entire ditional inventor.	

Page 3 of 12

LEGAL NA	ME OF INVERTOR(ASSIGNOR)			
Inventor:	Chun-Lung Chen	Date:	DEC 0 2 2014	
Signature:	Chun-lung Ken	and the state of t		

Page 4 of 12

Title of Invention:

METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

As the below named inventor, I here This declaration is directed to:	by declare that:			
☑ The attached application, or				
☐ United States application nu	mber	filed o	on	, or
☐ PCT international application	n number	file	ed on	delectronic delect
The above-identified application was	made or authorized to b	e made by me.		***************************************
I believe that I am the original invent application.	or or an original joint inve	entor of a claime	d invention in	ı the
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr	I false statement made in isonment of not more that	n this declaration an five (5) years,	ı is punishabl or both.	е
In consideration of the payment by	UNITED MICROELE CORP.	CTRONICS	having a po	ostal address of
No.3, Li-Hsin Road 2, Science	-Based Industrial Pa	ark, Hsin-Chu	City 300, 1	Гаiwan, R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	o I of the sum of One Dol ad valuable consideration	lar (\$ 1.00), the	receipt of whi	ich is hereby
I hereby sell, assign and transfer to A the entire right, title and interest in ar invention as above-identified applica- invention by the above application or substitutes, or extensions thereof, an	nd to any and all improve tion and, in and to, all Le any continuations, conti	ments which are tters Patent to b nuation-in-part.	e disclosed in e obtained fo divisions, ren	the r said ewals.
I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or en n this assignment;	cumbrance has	been or will b	e made or
I further covenant that ASSIGNEE w and documents relating to said inven known and accessible to I and will te related thereto and will promptly exec	ition and said Letters Pat stify as to the same in ar	ent and legal eq ny interference, l	uivalents as i	may be
representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	lication, said invention a cessary or desirable to o	nd said Letters F arry out the proj	Patent and sa	id f. (Date of signing)
Note: An application data sheet (PTC inventive entity, must accompany this	D/SB/14 or equivalent), ir s form. Use this form for	ncluding naming each additional	the entire	

Page 5 of 12

LEGAL NAME OF INVENTOR(ASSIGNOR)					
Inventor:	Kun-Yuan Liao	Date:	DEC 0 2 2014		
Signature:	Kun-Yuan	7			

Page 6 of 12

NPO#NAU-P2377-USA:0 CUST#UMCD-2014-0517 F#NPO-P0002E-US1201 DSC0-103U010562

Title of Invention:

METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	_filed on,	or
☐ PCT international application	n number	filed on	
The above-identified application was	made or authorized to be made	by me.	Principle and American
I believe that I am the original invent application.	or or an original joint inventor of a	a claimed invention in the	
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr	I false statement made in this ded isonment of not more than five (5	claration is punishable) years, or both.	
In consideration of the payment by	UNITED MICROELECTRON	VICS having a postal addr	ess of
No.3, Li-Hsin Road 2, Science	-Based Industrial Park, Hsi	n-Chu City 300, Taiwan,	R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, and for other good an		0), the receipt of which is here	eby
I hereby sell, assign and transfer to ASSIGNEE and the successors and assignees of the ASSIGNEE the entire right, title and interest in and to any and all improvements which are disclosed in the invention as above-identified application and, in and to, all Letters Patent to be obtained for said invention by the above application or any continuations, continuation-in-part, divisions, renewals, substitutes, or extensions thereof, and as to Letters Patent any reissue or re-examination thereof.			
I hereby covenant that no assignmer entered into which would conflict with	nt, sale, agreement or encumbran n this assignment;	ce has been or will be made o	or
I further covenant that ASSIGNEE will, upon its request, be provided promptly with all pertinent facts and documents relating to said invention and said Letters Patent and legal equivalents as may be known and accessible to I and will testify as to the same in any interference, litigation proceeding related thereto and will promptly execute and deliver to ASSIGNEE or its legal			
representatives any and all papers, instruments or affidavits required to apply for, obtain, maintain, issue and enforce said application, said invention and said Letters Patent and said equivalents thereof which may be necessary or desirable to carry out the proposes thereof. IN WINTNESS WHEREOF, I have hereunto set hand and seal this			
Note: An application data sheet (PTC inventive entity, must accompany this	D/SB/14 or equivalent), including s form. Use this form for each add	naming the entire ditional inventor.	

Page 7 of 12

REEL: 034411 FRAME: 0650

Inventor: Feng-Yi Chang

Date: DEC 0 2 2014

Signature: Feng-Yi Chang

Page 8 of 12

Title of Invention: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	_filed on,	or
☐ PCT international application	number	filed on	
The above-identified application was	s made or authorized to be made	by me.	
I believe that I am the original invent application.	or or an original joint inventor of a	a claimed invention in the	
I hereby acknowledge that any willful false statement made in this declaration is punishable under18 U.S.C. 1001 by fine or imprisonment of not more than five (5) years, or both.			
In consideration of the payment by	UNITED MICROELECTROI CORP.	NICS having a postal addr	ess of
No.3, Li-Hsin Road 2, Science	-Based Industrial Park, Hs	in-Chu City 300, Taiwan,	R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good ar	o I of the sum of One Dollar (\$ 1.0 and valuable consideration.	00), the receipt of which is her	eby
I hereby sell, assign and transfer to a the entire right, title and interest in an invention as above-identified applica invention by the above application of substitutes, or extensions thereof, ar	nd to any and all improvements w tion and, in and to, all Letters Pat rany continuations, continuation-	which are disclosed in the tent to be obtained for said in-part, divisions, renewals,	ΞE
I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or encumbrar n this assignment;	nce has been or will be made o	or
I further covenant that ASSIGNEE w and documents relating to said inver known and accessible to I and will te related thereto and will promptly exe	ition and said Letters Patent and stify as to the same in any interfe	legal equivalents as may be rence, litigation proceeding	S
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	plication, said invention and said L cessary or desirable to carry out	Letters Patent and said the proposes thereof.	signing)
Note: An application data sheet (PTC inventive entity, must accompany this			

Page 9 of 12

LEGAL NAM	VIE OF INVENTOR(ASSIGNOR)		
Inventor:	En-Chiuan Liou	Date:	DEC 0 2 2014
Signature:	En Chiam Lion		

Page 10 of 12

NPO#NAU-P2377-USA:0 CUST#UMCD-2014-0517

Title of Invention: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	filed on	, or
□ PCT international application number		filed on	***************************************
The above-identified application was	s made or authorized to be made	by me.	
I believe that I am the original invent application.	or or an original joint inventor of	a claimed invention in	n the
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr	Il false statement made in this de isonment of not more than five (eclaration is punishables) years, or both.	le
In consideration of the payment by	UNITED MICROELECTRO	NICS having a po	ostal address of
No.3, Li-Hsin Road 2, Science	e-Based Industrial Park, He	sin-Chu City 300,	Taiwan, R.O.C
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good ar	o I of the sum of One Dollar (\$ 1. ad valuable consideration.	00), the receipt of wh	ich is hereby
I hereby sell, assign and transfer to a the entire right, title and interest in a invention as above-identified applica invention by the above application of substitutes, or extensions thereof, ar	nd to any and all improvements watten and, in and to, all Letters Par any continuations, continuation	which are disclosed in Itent to be obtained fo -in-part, divisions, ren	i the or said newals.
I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or encumbra n this assignment;	nce has been or will b	oe made or
I further covenant that ASSIGNEE w and documents relating to said inven known and accessible to I and will te related thereto and will promptly exe	ition and said Letters Patent and stify as to the same in any interf	l legal equivalents as erence, litigation proc	mav be
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	dication, said invention and said cessary or desirable to carry out	Letters Patent and sa	iid f. (Date of signing)
Note: An application data sheet (PTC inventive entity, must accompany this	D/SB/14 or equivalent), including	naming the entire	

Page 11 of 12

LEGAL NAM	ME OF INVENTOR(A	aignor)		
Inventor:	Chieh-Te Chen		Date:	DEC 0 2 2014
Signature:	Chieh-Te	Gen		

Page 12 of 12

NPO#NAU-P2377-USA:0 CUST#UMCD-2014-0517

RECORDED: 12/07/2014

F#NPO-P0002E-US1201 DSC0-103U010562